

Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT404 (D2PAK) surface mountable plastic package intended for use in circuits where very high blocking voltage, high static and dynamic dV/dt and high dI/dt can occur. This "series C" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

#### 2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- Less sensitive gate for high noise immunity
- · Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Triggering in three quadrants only
- Very high voltage capability

### 3. Applications

- Compressor starting controls
- · General purpose motor control
- · Reversing induction motor controls e.g. vertical axis washing machines

### 4. Quick reference data

#### Table 1. Quick reference data

Cumphiel	Devenueten	Conditions	Miles	Turn	Max	Link
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	1000	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 102 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3	-	-	8	A
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ t <sub>p</sub> = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	65	A
		full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.7 ms	-	-	72	A
Tj	junction temperature		-	-	125	°C
Static chara	octeristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	6	35	mA

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#### **3Q Hi-Com Triac**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	13	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	23	35	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	20	50	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
Dynamic cha	racteristics	·				
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 670 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	1000	4000	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$    V_D = 400 \text{ V};  \text{T}_\text{j} = 125 ^\circ\text{C};  \text{I}_\text{T(RMS)} = 8 \text{ A}; \\                                  $	12	32	-	A/ms

# 5. Pinning information

Table 2. I	Pinning inf	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2-71
2	T2	main terminal 2		sym051
3	G	gate		Symoor
mb	T2	mounting base; main terminal 2		
			D2PAK (SOT404)	

## 6. Ordering information

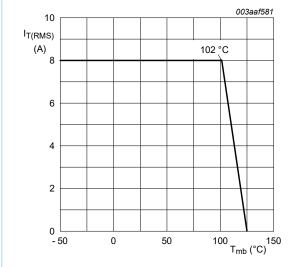
Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BTA208B-1000C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

### 7. Limiting values

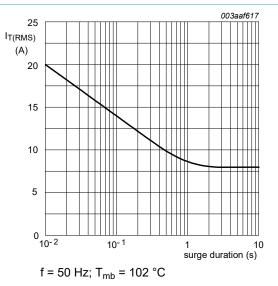
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	1000	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 102 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	8	A
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	-	65	A
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	72	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	21	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 70 mA	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

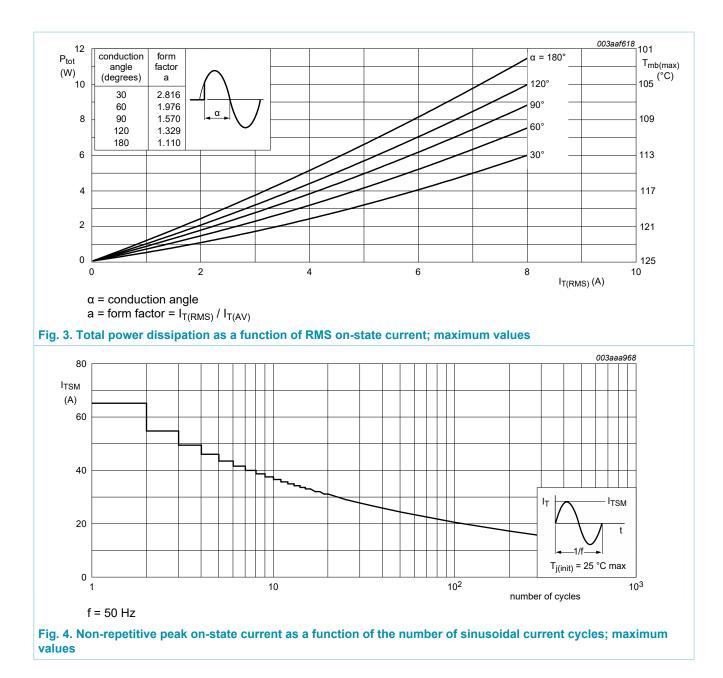






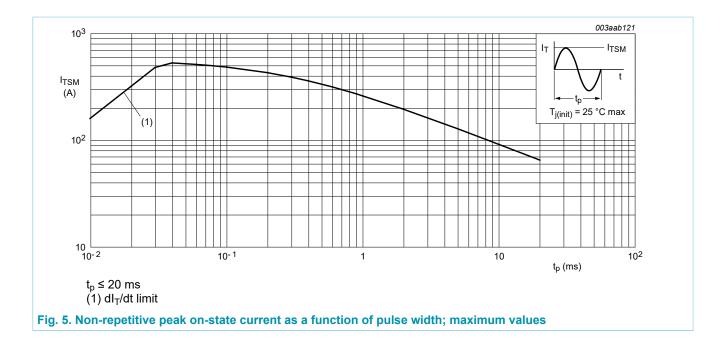


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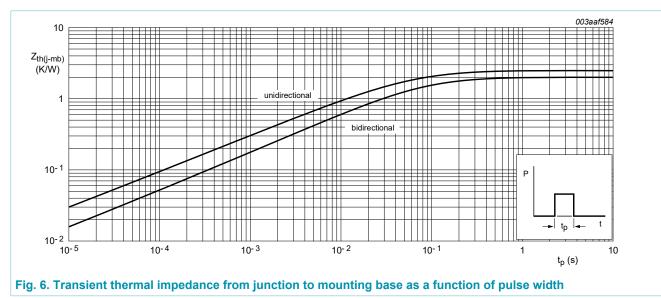
#### **3Q Hi-Com Triac**



**3Q Hi-Com Triac** 

### 8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	full cycle; <u>Fig. 6</u>	-	-	2	K/W
		half cycle; <u>Fig. 6</u>	-	-	2.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	55	-	K/W



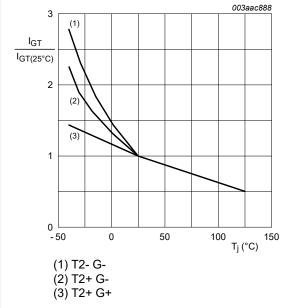
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## 9. Characteristics

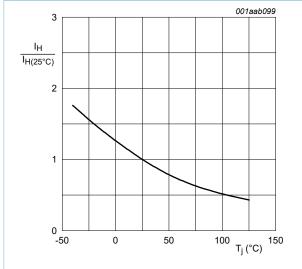
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		· · · ·			
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	6	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	13	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	23	35	mA
I <sub>L</sub> la	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	25	50	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	48	75	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	30	50	mA
I <sub>Н</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	20	50	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 1000 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics	· · · · ·				
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 670 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	1000	4000	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 8 A; dV <sub>com</sub> /dt = 20 V/µs; snubberless condition; gate open circuit; Fig. 12	12	32	-	A/ms
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 12 A; $V_D$ = 1000 V; $I_G$ = 0.1 A; d $I_G$ /dt = 5 A/µs	-	2	-	μs

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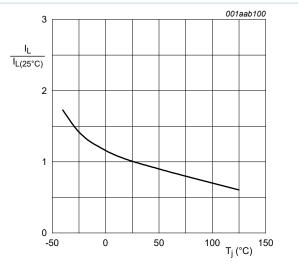
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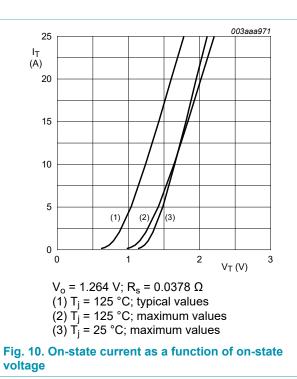






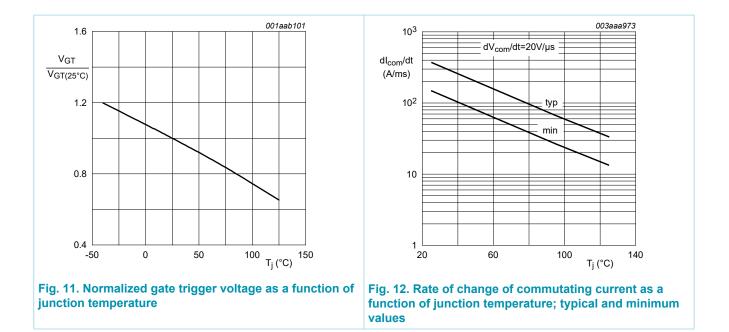






## BTA208B-1000C

#### **3Q Hi-Com Triac**



**3Q Hi-Com Triac** 

#### **10. Package outline**

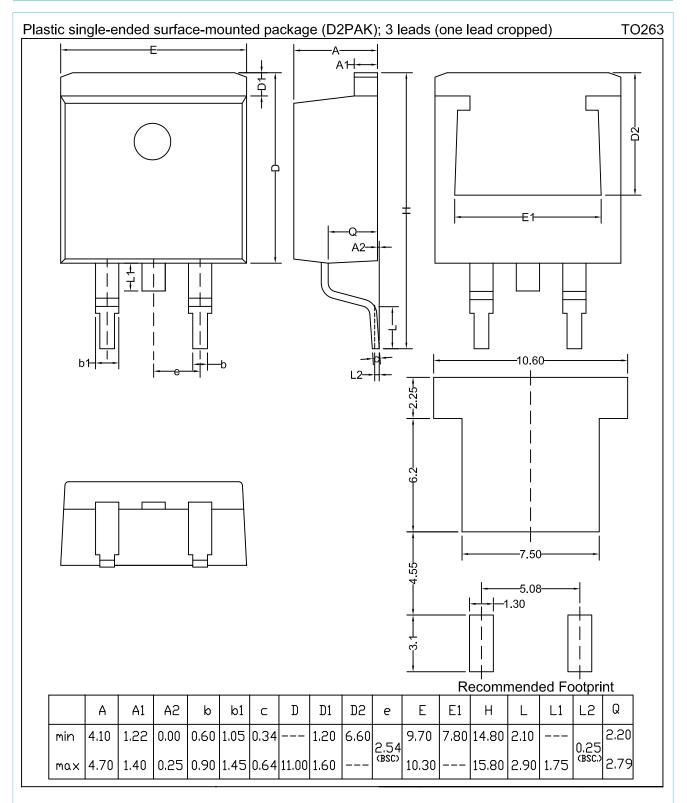


Fig. 13. Package outline D2PAK (SOT404)

#### **3Q Hi-Com Triac**

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#### **Data sheet status**

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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